

SPEC SHEET (FOR REFERENCE)	SHEET No. G05004	Rev. 3	Page. 1 of 1
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TYPE:6PT1002N1T

CHIP SIZE	1.1 * 1.1mm
WAFER SIZE	6 inch

Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-Source voltage	VDSS	20	V
Gate-Source voltage	VGSS	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT			UNIT	CONDITIONS
		MIN.	Typ	MAX.		
1	IGSS			±1	uA	VGS=±8V, VDS=0V
2	IDSS			500	nA	VDS=20V, VGS=0V
3	BVDSS	23			V	ID=100uA, VGS=0V
4	Vth	0.53		1	V	ID=1mA, VDS=10V
5	RDS(on)1		27	40	mΩ	ID=2.0A, VGS=4.5V
6	RDS(on)2		35	50	mΩ	ID=2.0A, VGS=2.5V
6	RDS(on)3		70	110	mΩ	ID=0.5A, VGS=1.8V
7	VSD		0.85	1.1	V	IS=2A, VGS=0V
8	Yfs		4		S	VDS=10V, ID=0.5A

※Built in ZD between Gate and Source

PHENITEC SEMICONDUCTOR Corp.